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November 2013

FQPF70N10

N-Channel QFET[®] MOSFET 100 V, 35 A, 23 m Ω

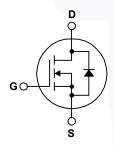
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 35 A, 100 V, $R_{DS(on)}$ = 23 m Ω (Max.) @ V_{GS} = 10 V, I_D = 17.5 A
- Low Gate Charge (Typ. 85 nC)
- Low Crss (Typ. 150 pF)
- · 100% Avalanche Tested
- · 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQPF70N10	Unit
V _{DSS}	Drain-Source Voltage		100	V
I _D	Drain Current - Continuous (T _C = 25°C	C)	35	Α
	- Continuous (T _C = 100°	°C)	24.7	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	140	Α
V_{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1300	mJ
I _{AR}	Avalanche Current	(Note 1)	35	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	6.2	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
P _D	Power Dissipation (T _C = 25°C)		62	W
	- Derate above 25°C		0.41	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temperature for Soldering	ng, 300		°C
٠.٢	1/8" from Case for 5 seconds		300	

Thermal Characteristics

Symbol	Parameter	FQPF70N10	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.42	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF70N10	FQPF70N10	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.1		V/°(
I _{DSS} Zero Gate Voltage Drain Current	Zara Cata Valtaga Drain Current	V _{DS} = 100 V, V _{GS} = 0 V			1	μΑ
	V _{DS} = 80 V, T _C = 150°C			10	μΑ	
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V			100	nΑ
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = - 25 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 17.5 A		0.019	0.023	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 17.5 A	\	38		S
Dynam	ic Characteristics					
	ic Ollaracteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		2500	3300	pF
C _{iss}		$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		2500 720	3300 940	_ '
C _{iss} C _{oss} C _{rss}	Input Capacitance					pF pF
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance			720	940	pF
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	f = 1.0 MHz		720	940	pF
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance ng Characteristics	f = 1.0 MHz V _{DD} = 50 V, I _D = 70 A,		720 150	940	pF pF
C_{iss} C_{oss} C_{rss} Switchi $t_{d(on)}$ t_r	Input Capacitance Output Capacitance Reverse Transfer Capacitance Ing Characteristics Turn-On Delay Time	f = 1.0 MHz $V_{DD} = 50 \text{ V}, I_{D} = 70 \text{ A},$ $R_{G} = 25 \Omega$		720 150	940 200 70	pF pF
C_{iss} C_{oss} C_{rss} Switchi $t_{d(on)}$ t_r $t_{d(off)}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance Ing Characteristics Turn-On Delay Time Turn-On Rise Time	f = 1.0 MHz V _{DD} = 50 V, I _D = 70 A,		720 150 30 470	940 200 70 950	pF pF ns
$\begin{aligned} & C_{iss} \\ & C_{oss} \\ & C_{rss} \end{aligned}$ $& Switchi \\ & t_{d(on)} \\ & t_r \\ & t_{d(off)} \end{aligned}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance Ing Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time	f = 1.0 MHz $V_{DD} = 50 \text{ V}, I_{D} = 70 \text{ A},$ $R_{G} = 25 \Omega$	 	720 150 30 470 130	940 200 70 950 270	pF pF
C _{iss} C _{oss} C _{rss} Switchi	Input Capacitance Output Capacitance Reverse Transfer Capacitance Ing Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time	f = 1.0 MHz V_{DD} = 50 V, I_{D} = 70 A, R_{G} = 25 Ω (Note 4)	 	720 150 30 470 130 160	940 200 70 950 270 330	pF pF ns ns

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		 	35	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		 	140	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 35 A	 	1.5	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 V, I_{S} = 70 A,$	 110		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs	 430	/	nC

- **Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 1.59 mH, I_{AS} = 35 A, V_{DD} = 25 V, R_{G} = 25 Ω , starting T_{J} = 25°C. 3. I_{SD} \leq 70 A, di/dt \leq 300 A/µs, V_{DD} \leq BV $_{DSS}$, starting T_{J} = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

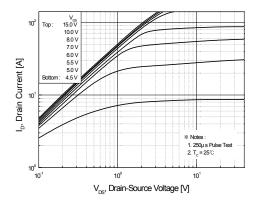


Figure 1. On-Region Characteristics

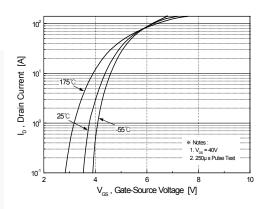


Figure 2. Transfer Characteristics

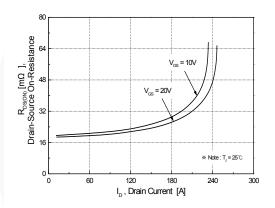


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

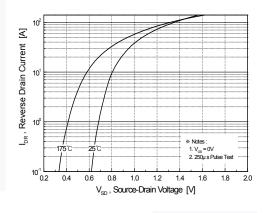


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

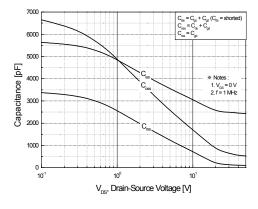


Figure 5. Capacitance Characteristics

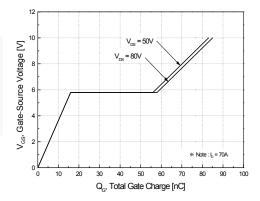
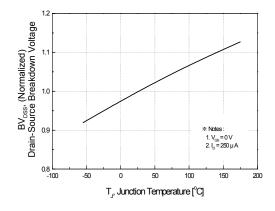


Figure 6. Gate Charge Characteristics

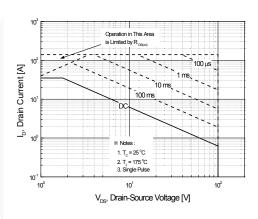
Typical Characteristics (continued)



3.0 (paging 2.5 (paging 2.0

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



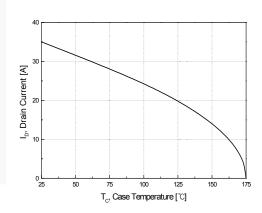


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

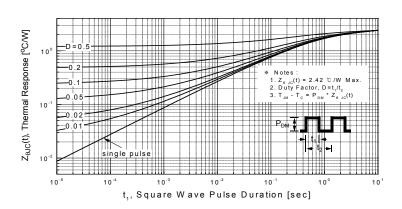


Figure 11. Transient Thermal Response Curve

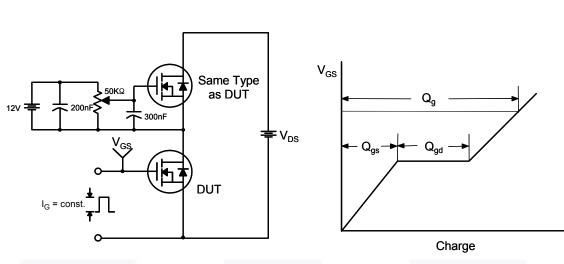


Figure 12. Gate Charge Test Circuit & Waveform

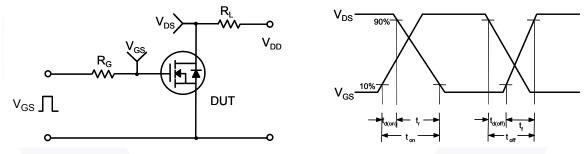


Figure 13. Resistive Switching Test Circuit & Waveforms

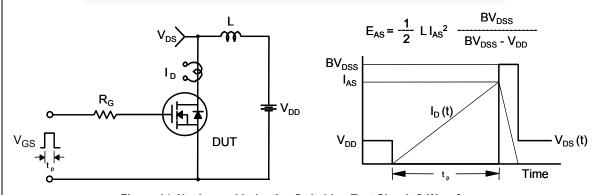
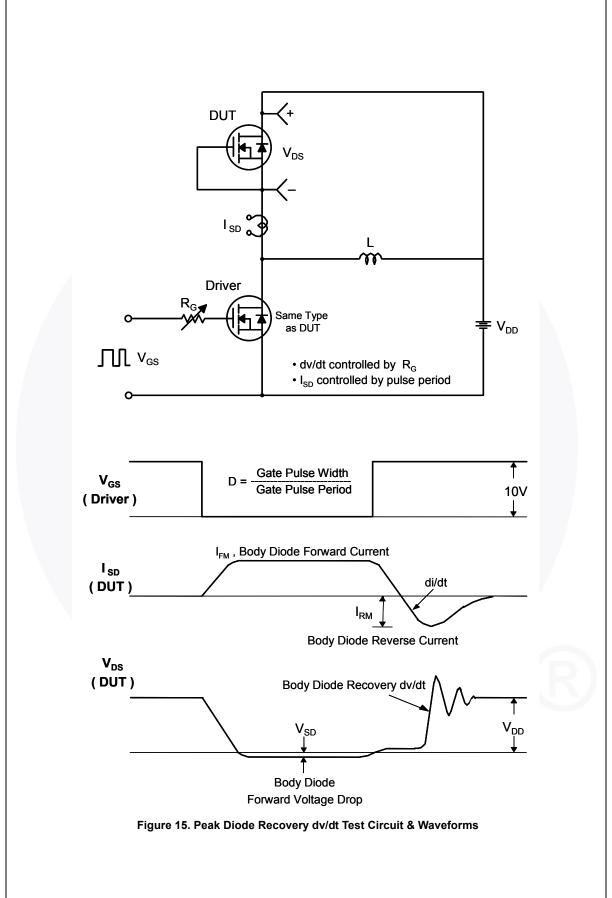


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

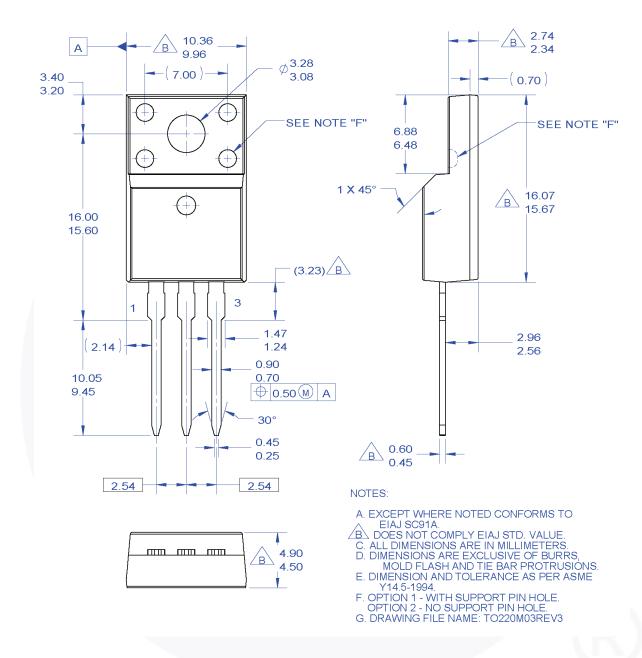


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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